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**Electron Stimulated Decomposition of Acetylene as a Precursor for Graphene** MAHESH KUMAR, National Physical Laboratory, New Delhi, SARA ROTHWELL, PHILIP COHEN, University of Minnesota — We report here on the deposition of carbon via  $C_2H_2$  dissociation by electron beam irradiation and thermal decomposition. The substrates investigated include sapphire, silicon, ALD deposited  $Al_2O_3/SiO_2$ , and GaN/sapphire. Raman analyses show that on C-plane sapphire both thermal decomposition and electron beam stimulated dissociation of  $C_2H_2$  deposit carbon successfully. On other substrates these methods were inactive, showing the decomposition of  $C_2H_2$  on sapphire is catalytic. We tested different annealing times and  $C_2H_2$  pressures, gauging absorption saturation with RHEED. Samples exposed to 15 min.  $C_2H_2$  adsorption during 400 eV electron irradiation and then annealed for 2 hr. to above  $600^\circ C$  in high vacuum showed the greatest proportion of sp<sup>2</sup> to sp<sup>3</sup> bonding by Raman analysis. The Raman spectra also suggest hydrogen adsorption, which may hinder further sp<sup>2</sup> bonding. Annealing samples in a hydrogen atmosphere does not change their Raman spectra, suggesting hydrogen saturation. Partial support from the University of Minnesota Institute for Renewable Energy and the Environment

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